

Title (en)

LOW-TEMPERATURE PROCESS FOR FORMING AN EPITAXIAL LAYER ON A SEMICONDUCTOR SUBSTRATE

Title (de)

NIEDRIGTEMPERATURVERFAHREN ZUR HERSTELLUNG EPITAKTISCHER SCHICHTEN AUF EIN HALBLEITERSUBSTRAT

Title (fr)

PROCEDE BASSE TEMPERATURE PERMETTANT DE FORMER UNE COUCHE EPITAXIALE SUR UN SUBSTRAT SEMICONDUCTEUR

Publication

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Application

**EP 99945264 A 19990826**

Priority

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Abstract (en)

[origin: WO0012785A1] A low temperature process for forming an epitaxial layer on a workpiece surface, without requiring ultrahigh vacuum or ultraclean conditions in the processing chamber during formation of the epitaxial layer. The process further allows for the simultaneous formation of an epitaxial layer on a plurality of workpieces (28). The workpieces are placed in chamber (12) with multi controlled heater (212) and controllers (308 and 306). The gas (250) is supplied via a pipe and panel (248) to control flow.

IPC 1-7

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IPC 8 full level

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